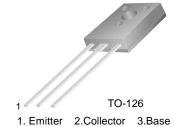


### **KSB772**

#### **Audio Frequency Power Amplifier**

- Low Speed Switching
- Complement to KSD882



## **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	- 40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 30	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current (DC)	- 3	А
I <sub>CP</sub>	*Collector Current (Pulse)	- 7	А
I <sub>B</sub>	Base Current (DC)	- 0.6	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	10	W
	Collector Dissipation (T <sub>a</sub> =25°C)	1	W
$R_{\theta ja}$	Junction to Ambient	132	°C/W
$R_{\theta jc}$	Junction to Case	13.5	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty Cycle≤50%

#### Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -30V, I_{E} = 0$			- 1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -3V, I_{C} = 0$			- 1	μΑ
h <sub>FE1</sub>	* DC Current Gain	$V_{CE} = -2V, I_{C} = -20mA$	30	220		
$h_{FE2}$		$V_{CE} = -2V, I_{C} = -1A$	60	160	400	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = -2A, I_B = -0.2A$		- 0.3	- 0.5	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = -2A, I_B = -0.2A$		- 1.0	- 2.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{E} = -0.1A$		80		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_{E} = 0$ f = 1MHz		55		pF

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2%

## $h_{\mbox{\scriptsize FE}}$ Classification

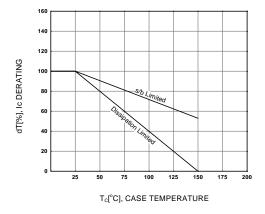
Classification	R	0	Y	G
h <sub>FE2</sub>	60 ~ 120	100 ~ 200	160 ~ 320	200 ~ 400

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# **Typical Characteristics** $V_{CE} = -2V$ [A], COLLECTOR CURRENT -10mA hre, DC CURRENT GAIN $I_{R} = -6mA$ $I_{B} = -1mA$ $I_{\text{c}}[\text{mA}]$ , COLLECTOR CURRENT $V_{CE}[V]$ , COLLECTOR-EMITTER VOLTAGE Figure 1. Static Characteristic Figure 2. DC current Gain Vce(sat), VBE (sat) [mV] SATURATION VOLTAGE -100 C<sub>∞</sub>[pF], CAPACITANCE -100 V<sub>CE</sub>(sat) Ic[mA], COLLECTOR CURRENT $V_{CR}[V]$ , COLLECTOR-BASE VOLTAGE Figure 3. Base-Emitter Saturation Voltage **Figure 4. Collector Output Capacitance** Collector-Emitter Saturation Voltage f<sub>f</sub>[MHz], CURRENT GAIN BANDWIDTH PRODUCT MAX(Pulse I,[A], COLLECTOR CURRENT MAX -0.01 L -1 Ic[A], COLLECTOR CURRENT $V_{CE}[V]$ , COLLECTOR-EMITTER VOLTAGE Figure 5. Current Gain Bandwidth Product Figure 6. Safe Operating Area

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# **Typical Characteristics** (Continued)



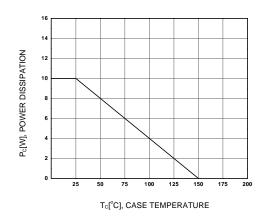
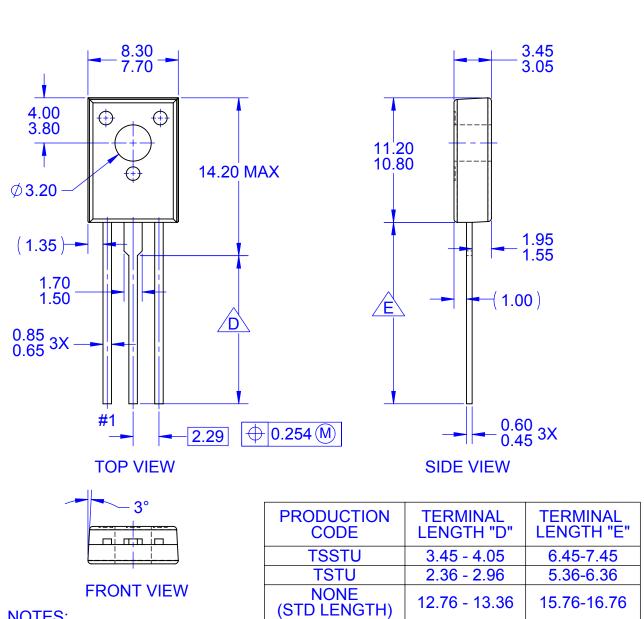


Figure 7. Derating Curve of Safe Operating Areas

Figure 8. Power Derating

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- **NOTES:**
- A. NO INDUSTRY STANDARD APPLIES TO THIS **PACKAGE**
- B. ALL DIMENSIONS ARE IN MILLIMETERS
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS





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